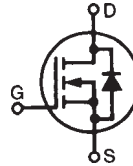


# PolarHV™ HiPerFET IXFR 36N60P

## Power MOSFET

(Electrically Isolated Back Surface)

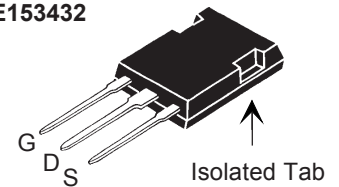
N-Channel Enhancement Mode  
Avalanche Rated  
Fast Intrinsic Diode



$V_{DSS}$	=	600	V
$I_{D25}$	=	20	A
$R_{DS(on)}$	≤	200	mΩ
$t_{rr}$	≤	200	ns

Symbol	Test Conditions	Maximum Ratings	
$V_{DSS}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V
$V_{DGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GS} = 1\text{ M}\Omega$	600	V
$V_{GSS}$	Continuous	±30	V
$V_{GSM}$	Transient	±40	V
$I_{D25}$	$T_C = 25^\circ\text{C}$	20	A
$I_{DM}$	$T_C = 25^\circ\text{C}$ , pulse width limited by $T_{JM}$	80	A
$I_{AR}$	$T_C = 25^\circ\text{C}$	36	A
$E_{AR}$	$T_C = 25^\circ\text{C}$	50	mJ
$E_{AS}$	$T_C = 25^\circ\text{C}$	1.5	J
$dv/dt$	$I_S \leq I_{DM}$ , $di/dt \leq 100\text{ A}/\mu\text{s}$ , $V_{DD} \leq V_{DSS}$ , $T_J \leq 150^\circ\text{C}$ , $R_G = 2\ \Omega$	20	V/ns
$P_D$	$T_C = 25^\circ\text{C}$	208	$^\circ\text{C}$
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$T_L$	1.6 mm (0.062 in.) from case for 10 s	300	$^\circ\text{C}$
$T_{SOLD}$	Plastic body for 10 s	260	$^\circ\text{C}$
$V_{ISOL}$	50/60 Hz, RMS, 1 minute	2500	V~
$F_C$	Mounting force	20..120/4.6..27	N/lb
<b>Weight</b>		5	g

ISOPLUS247 (IXFR)  
E153432



G = Gate    D = Drain  
S = Source

### Features

- 1 Silicon chip on Direct-Copper-Bond substrate
- High power dissipation
- Isolated mounting surface
- 2500V electrical isolation
- 1 International standard package
- 1 Fast recovery diode
- 1 Unclamped Inductive Switching (UIS) rated
- 1 Low package inductance
- easy to drive and to protect

Symbol	Test Conditions	Characteristic Values		
		Min.	Typ.	Max.
$BV_{DSS}$	$V_{GS} = 0\text{ V}$ , $I_D = 250\ \mu\text{A}$	600		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$ , $I_D = 4\text{ mA}$	3.0		5.0 V
$I_{GSS}$	$V_{GS} = \pm 30\text{ V}$ , $V_{DS} = 0\text{ V}$			±100 nA
$I_{DSS}$	$V_{DS} = V_{DSS}$ $V_{GS} = 0\text{ V}$ $T_J = 125^\circ\text{C}$			25 $\mu\text{A}$ 250 $\mu\text{A}$
$R_{DS(on)}$	$V_{GS} = 10\text{ V}$ , $I_D = I_T$ (note 1) Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			200 mΩ

### Advantages

- 1 Easy to mount
- 1 Space savings
- 1 High power density

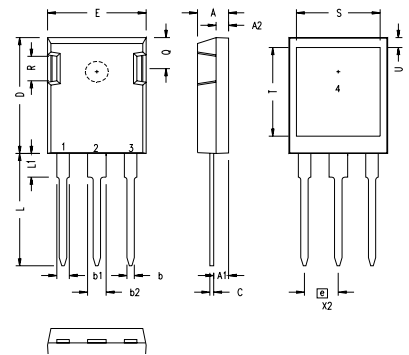
Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$g_{fs}$	$V_{DS} = 20\text{ V}$ ; $I_D = I_T$ , pulse test	25	40	S
$C_{iss}$	$V_{GS} = 0\text{ V}$ , $V_{DS} = 25\text{ V}$ , $f = 1\text{ MHz}$		5800	pF
$C_{oss}$			570	pF
$C_{rss}$			30	pF
$t_{d(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = I_T$ $R_G = 2\ \Omega$ (External)		30	ns
$t_r$			25	ns
$t_{d(off)}$			80	ns
$t_f$			22	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}$ , $V_{DS} = 0.5 V_{DSS}$ , $I_D = I_T$		102	nC
$Q_{gs}$			34	nC
$Q_{gd}$			36	nC
$R_{thJC}$			0.6	$^\circ\text{C/W}$
$R_{thCS}$		0.15		$^\circ\text{C/W}$

Note 1: Test current  $I_T = 18\text{ A}$

### Source-Drain Diode

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		Min.	Typ.	Max.
$I_S$	$V_{GS} = 0\text{ V}$			36 A
$I_{SM}$	Repetitive			80 A
$V_{SD}$	$I_F = I_S$ , $V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.5 V
$t_{rr}$	$I_F = 25\text{ A}$ , $-di/dt = 100\text{ A}/\mu\text{s}$ $V_R = 100\text{ V}$ , $V_{GS} = 0\text{ V}$			200 ns
$Q_{RM}$			0.8	$\mu\text{C}$
$I_{RM}$			6.0	A

### ISOPLUS247 (IXFR) Outline



SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.190	.205	4.83	5.21
A1	.090	.100	2.29	2.54
A2	.075	.085	1.91	2.16
b	.045	.055	1.14	1.40
b1	.075	.084	1.91	2.13
b2	.115	.123	2.92	3.12
C	.024	.031	0.61	0.80
D	.819	.840	20.80	21.34
E	.620	.635	15.75	16.13
e	.215 BSC		5.45 BSC	
L	.780	.800	19.81	20.32
L1	.150	.170	3.81	4.32
Q	.220	.244	5.59	6.20
R	.170	.190	4.32	4.83
S	.520	.540	13.21	13.72
T	.620	.640	15.75	16.26
U	.065	.080	1.65	2.03

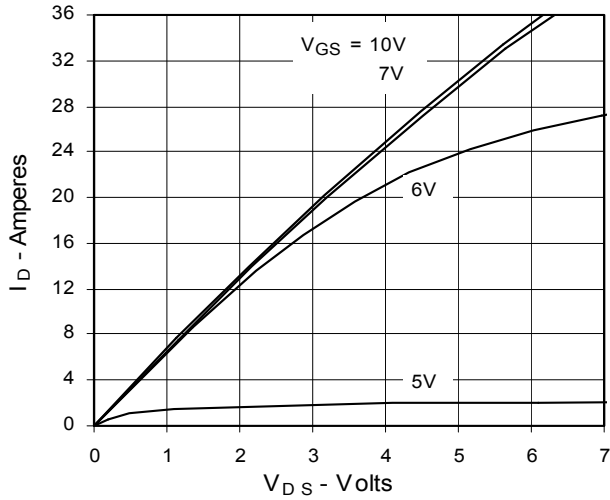
- 1 - GATE
- 2 - DRAIN (COLLECTOR)
- 3 - SOURCE (EMITTER)
- 4 - NO CONNECTION

NOTE: This drawing will meet all dimensions requirement of JEDEC outline TO-247AD except screw hole.

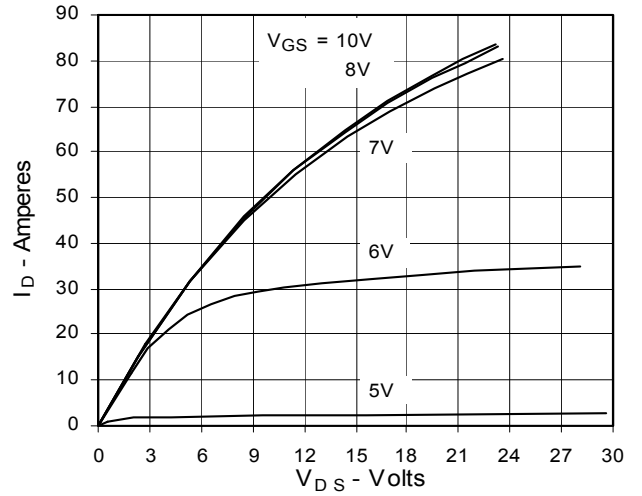
IXYS reserves the right to change limits, test conditions, and dimensions.

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4,881,106 5,034,796 5,187,117 5,486,715 6,306,728 B1 6,583,505 6,710,463 6,771,478 B2

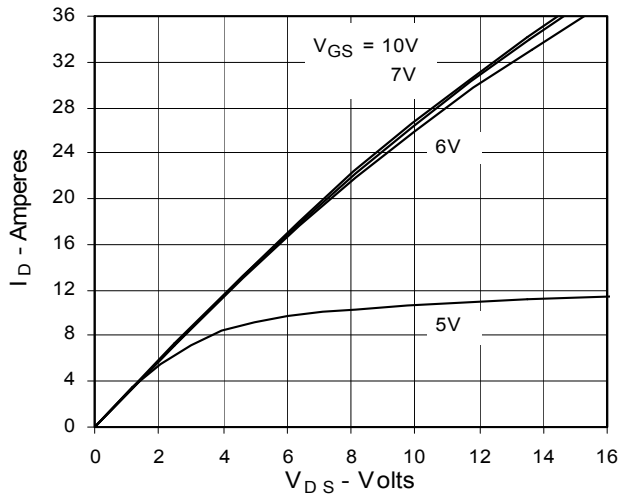
**Fig. 1. Output Characteristics @ 25°C**



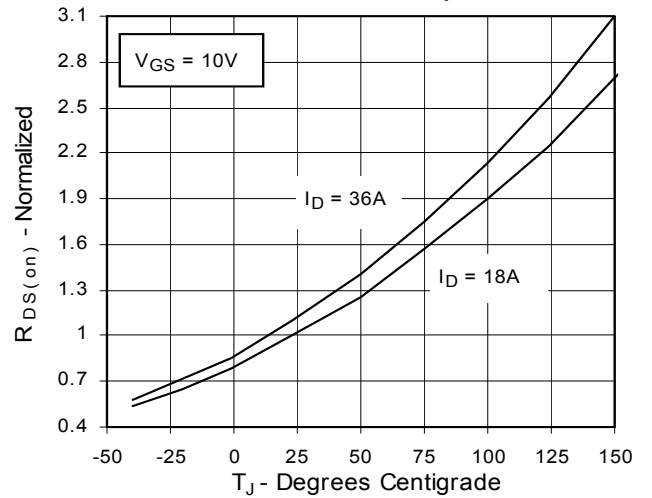
**Fig. 2. Extended Output Characteristics @ 25°C**



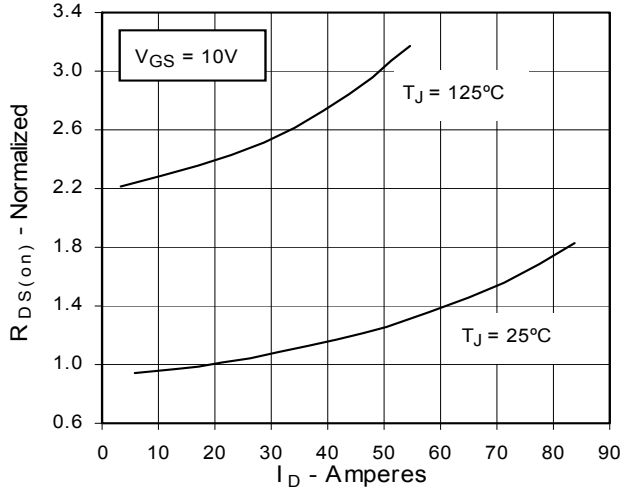
**Fig. 3. Output Characteristics @ 125°C**



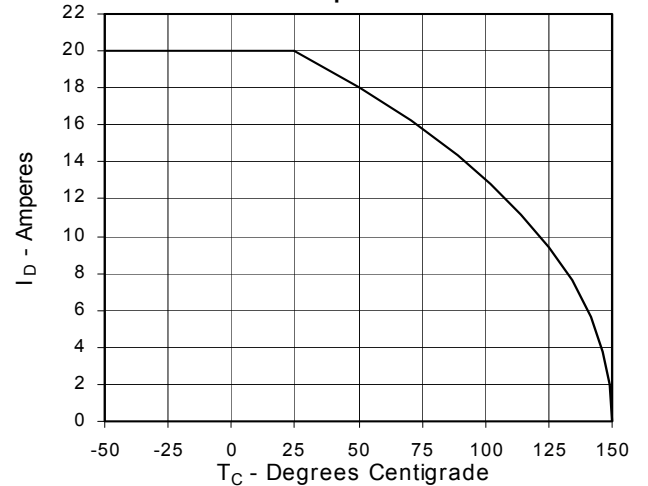
**Fig. 4.  $R_{DS(on)}$  Normalized to  $I_D = 18A$  Value vs. Junction Temperature**



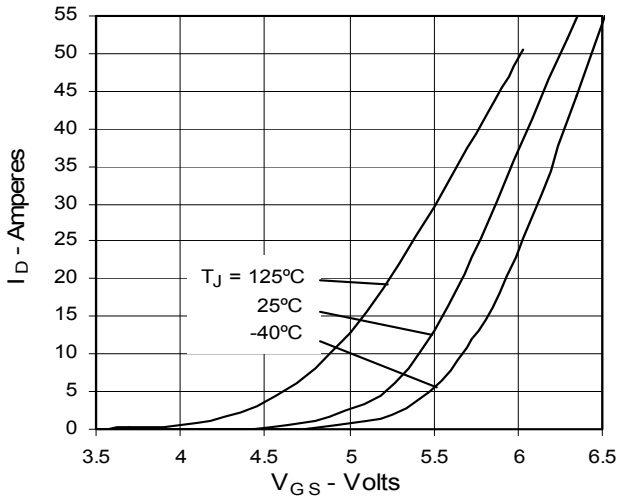
**Fig. 5.  $R_{DS(on)}$  Normalized to  $I_D = 18A$  Value vs.  $I_D$**



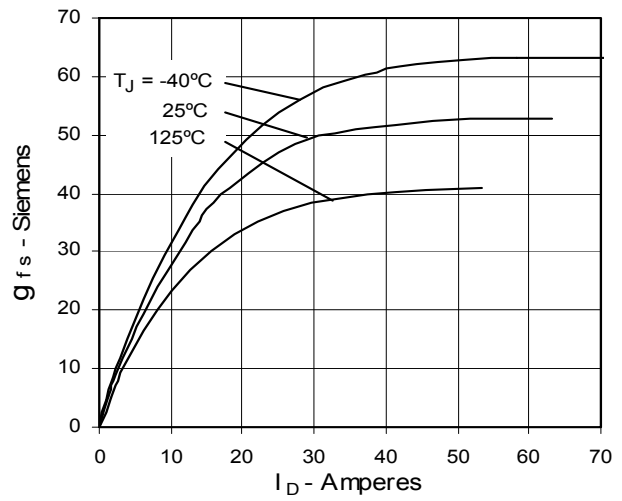
**Fig. 6. Drain Current vs. Case Temperature**



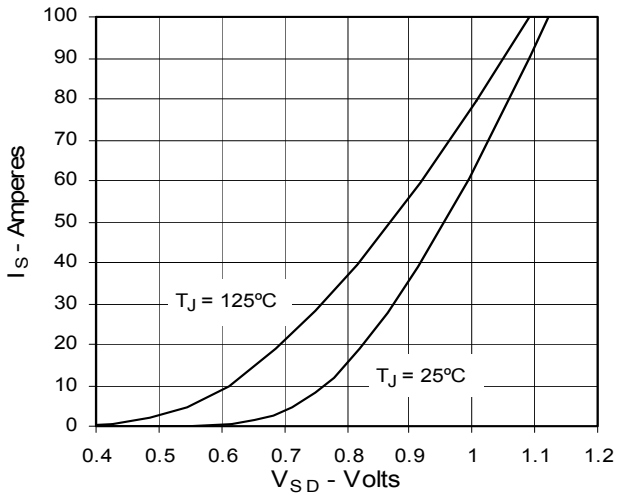
**Fig. 7. Input Admittance**



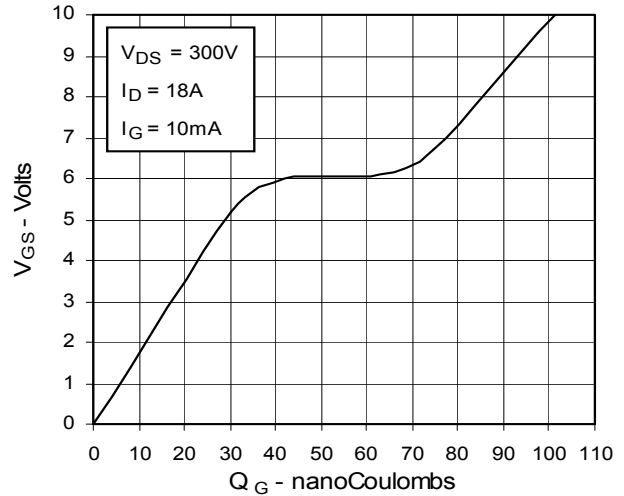
**Fig. 8. Transconductance**



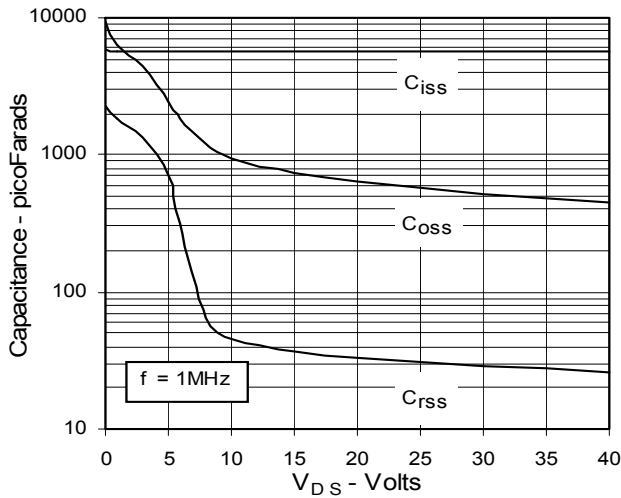
**Fig. 9. Source Current vs. Source-To-Drain Voltage**



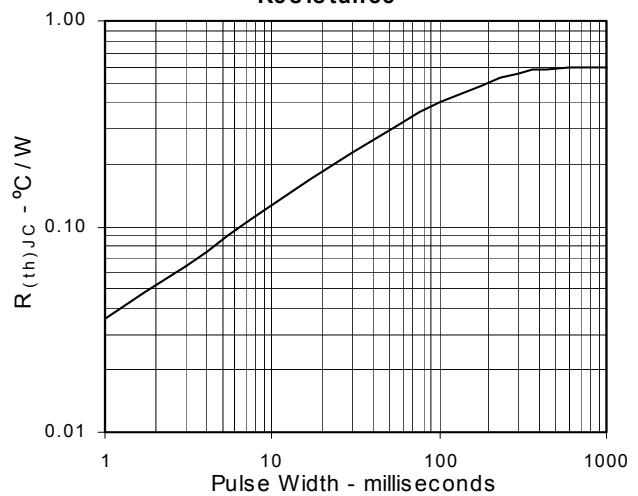
**Fig. 10. Gate Charge**



**Fig. 11. Capacitance**



**Fig. 12. Maximum Transient Thermal Resistance**





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